00-001

GAU 2812

April 12, 2001

#3 1/2
8-22-02
Payton

TO: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
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Subject:

Serial No. 09/773,872 02/02/01

Richard Bullock, David P. Jones

METHOD OF FABRICATING A GATE DIELECTRIC LAYER FOR A THIN FILM TRANSISTOR

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,124,171 to Arghavani et al., "Method of Forming Gate Oxide Having Dual Thickness by Oxidation Process", discusses a dual gate oxide process.

U.S. Patent 6,121,095 to Tai et al., "Method for Fabricating Gate Oxide", discusses a N anneal of a gate oxide.

The following five U.S. Patents disclose gate oxide processes:

1) U.S. Patent 6,124,210 to Chino et al., "Method of Cleaning Surface of Substrate and Method of Manufacturing Semiconductor Device".

2) U.S. Patent 6,040,207 to Gardner et al., "Oxide Formation Technique Using Thin Film Silicon Deposition".

3) U.S. Patent 5,940,736 to Brady et al., "Method for Forming a High Quality Ultrathin Gate Oxide Layer".

4) U.S. Patent 5,712,208 to Tseng et al., "Methods of Formation of Semiconductor Composite Gate Dielectric Having Multiple Incorporated Atomic Dopants".

5) U.S. Patent 4,851,370 to Doklan et al., "Fabricating a Semiconductor Device with Low Defect Density Oxide".

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

OIPE JC03 APR 23 2001 PATENT & TRADEMARK OFFICE

Sheet 1 of 1 #3/2

Docket Number (Optional)	Application Number
ESM-00-001	09/773,872
Applicant: Richard Bullock et al.	
Filing Date: 02/02/01	Group Art Unit: 2812

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	6124171	9/26/00	Arghavani et al.	438	286	9/24/98
	6121095	9/19/00	Tai et al.	438	287	11/13/98
	6124210	9/26/00	Chino et al.	438	706	5/24/99
	6040207	3/21/00	Gardner et al.	438	216	11/10/98
	5944073	6/17/99	Brady et al.	438	787	3/11/97
	5712208	1/27/98	Tseng et al.	438	770	5/25/95
	4851370	7/25/89	Doklan et al.	437	225	12/28/87

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through